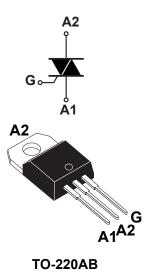


12 A 800 V logic level Triac in TO-220AB package



Features

- Medium current Triac
- · Three quadrants
- ECOPACK2 compliant

Applications

- General purpose AC line load switching
- Motor control circuits
- Small home appliances
- Lighting
- · Inrush current limiting circuits
- Overvoltage crowbar protection

Description

Available in through-hole package, the T1210T-8T Triac can be used for the on/off or phase angle control function in general purpose AC switching.

This device can be directly driven by a microcontroller due to its 10 mA gate current requirement.

Product status link
T1210T-8T

Product summary				
Order code	T1210T-8T			
Package	TO-220AB			
I _{T(RMS)}	12 A			
V_{DRM}/V_{RRM}	800 V			
V _{DSM} /V _{RSM}	900 V			
I _{GT}	10 mA			



1 Characteristics

Table 1. Absolute maximum ratings (limiting values)

Symbol	Parameter	Value	Unit		
I _{T(RMS)}	On-state RMS current (full sine wave)	T _c = 131 °C	12	Α	
I	Non repotitive surge peak on state surrent (T. initial = 25 °C)	t = 20 ms	90	Α	
I _{TSM}	Non repetitive surge peak on-state current (T _j initial = 25 °C)	F = 60 Hz	t = 16.7 ms	95	A
l ² t	l ² t value for fusing, (T _j initial = 25 °C)	·	t _p = 10 ms	54	A ² s
\/	5	T _j = 150 °C	600	V	
V _{DRM} /V _{RRM}	Repetitive surge peak off-state voltage	T _j = 125 °C	800		
V _{DSM} /V _{RSM}	Non repetitive surge peak off-state voltage $t_p = 10 \text{ ms}$				V
dl/dt	Critical rate of rise of on-state current $G = 2 \times I_{GT}$, tr $\leq 100 \text{ ns}$		F = 100 Hz	100	A/µs
I _{GM}	Peak gate current $t_p = 20 \mu s$ $T_j = 150$		T _j = 150 °C	4	Α
P _{G(AV)}	Average gate power dissipation $T_j = 150 ^{\circ}\text{C}$				W
T _{stg}	Storage junction temperature range				°C
Tj	Operating junction temperature range			-40 to +150	°C
TL	Maximum lead temperature soldering during 10 s				°C

Table 2. Electrical characteristics ($T_j = 25$ °C unless otherwise specified)

Symbol	Test condition	ons			Unit
I _{GT} ⁽¹⁾	$V_D = 12 \text{ V}, R_L = 30 \Omega$	1 - 11 - 111	Min.	0.5	mA
'GI\'	VD = 12 V, NL = 30 22	1 - 11 - 111	Max.	10	
V_{GT}	$V_D = 12 \text{ V}, R_L = 30 \Omega$	1 - 11 - 111	Max.	1.3	V
V_{GD}	$V_D = V_{DRM}$, $R_L = 3.3 \text{ k}\Omega$, $T_j = 150 ^{\circ}\text{C}$	1 - 11 - 111	Min.	0.2	V
I _H ⁽¹⁾	I _T = 500 mA	·	Max.	15	mA
	I _G = 1.2 x I _{GT}	1 - 111	Max.	20	mA
lL	IG - 1.2 X IG	II	IVIAX.	25	
dV/dt ⁽¹⁾	V _D = V _R = 536 V, gate open	T _j = 125 °C	Min.	250	\//ug
	V _D = V _R = 402 V, gate open	T _j = 150 °C	IVIIII.	170	V/µs
(dl/dt)c ⁽¹⁾	(4)//41/2 = 0.4.1///	T _j = 125 °C		11.7	
	(dV/dt)c = 0.1 V/μs	T _j = 150 °C	Min	8.2	A/ms
	(4)/(4)/2 = 10)////2	T _j = 125 °C	Min.	6.0	
	(dV/dt)c = 10 V/μs	T _j = 150 °C		2.7	

^{1.} For both polarities of A2 referenced to A1

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Table 3. Static characteristics

Symbol	Tes	Test conditions		Value	Unit
$V_T^{(1)}$ $I_{TM} = 17 \text{ A, } t_p = 380 \mu\text{s}$		T _j = 25 °C	Max.	1.55	V
V _{TO} ⁽¹⁾	Threshold voltage	T _j = 150 °C	Max.	0.85	V
R _d ⁽¹⁾	Dynamic resistance	T _j = 150 °C	Max.	37	mΩ
	V _D = V _R = 800 V	T _j = 25 °C	May	7.5	μA
I _{DRM} , I _{RRM}	vD - vR - 000 v	T _j = 125 °C	Max.	1.0	mA
	V _D = V _R = 600 V	T _j = 150 °C	Max.	2.7	IIIA

^{1.} For both polarities of A2 referenced to A1

Table 4. Thermal parameters

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case (AC)	1.3	°C/W
R _{th(j-a)}	Junction to ambient	60	°C/W



1.1 Characteristics (curves)

Figure 1. Maximum power dissipation versus on-state RMS current

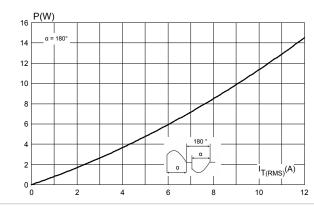


Figure 2. On-state RMS current versus case temperature

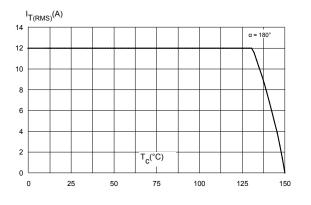


Figure 3. On-state RMS current versus ambient temperature (free air convection)

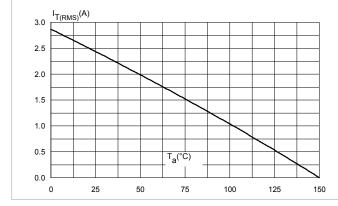


Figure 4. Relative variation of thermal impedance versus pulse duration

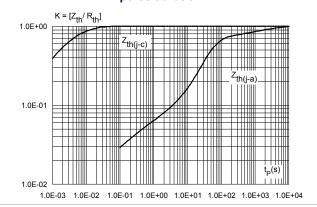


Figure 5. Relative variation of gate trigger voltage and current versus junction temperature (typical values)

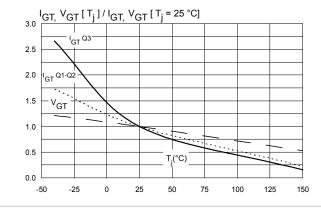
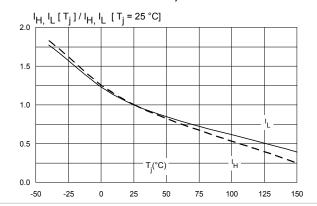


Figure 6. Relative variation of holding current and latching current versus junction temperature (typical values)



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Figure 7. Surge peak on-state current versus number of cycles

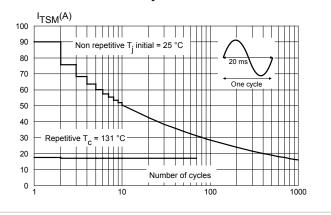


Figure 8. Non repetitive surge peak on-state current for a sinusoidal pulse with width tp < 10 ms

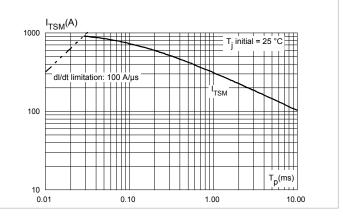


Figure 9. On-state characteristics (maximum values)

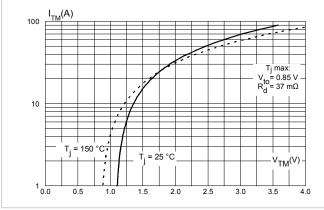


Figure 10. Relative variation of critical rate of decrease of main voltage versus junction temperature

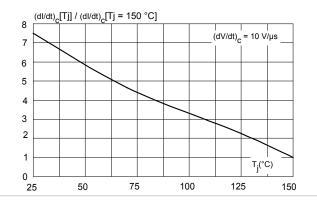


Figure 11. Relative variation of static dV/dt immunity versus junction temperature (maximum values)

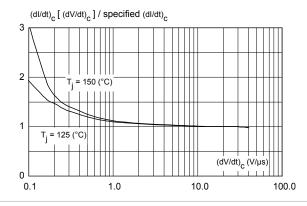
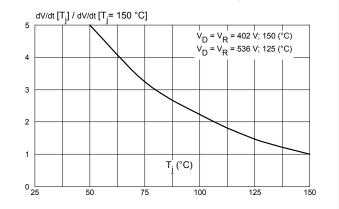


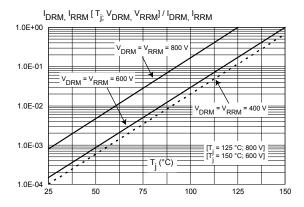
Figure 12. Relative variation of critical rate of decrease of main current versus reapplied dV/dt (typical values)



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Figure 13. Relative variation of leakage current versus junction temperature for different values of blocking voltage



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2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

2.1 TO-220AB package information

- Epoxy resin is halogen free and meets UL94 flammability standard, level V0
- Lead-free plating package leads
- Recommended torque: 0.4 to 0.6 N·m

В b2 Resin gate 0.5 mm max. protusion(1) F Α 14 13 c2 а1 12 a2 Μ с1 b1 Resin gate 0.5 mm max. protusion⁽¹⁾

Figure 14. TO-220AB package outline

(1)Resin gate position accepted in one of the two positions or in the symmetrical opposites.

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Table 5. TO-220AB package mechanical data

	Dimensions						
Ref.	Millimeters			Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
А	15.20		15.90	0.5984		0.6260	
a1		3.75			0.1476		
a2	13.00		14.00	0.5118		0.5512	
В	10.00		10.40	0.3937		0.4094	
b1	0.61		0.88	0.0240		0.0346	
b2	1.23		1.32	0.0484		0.0520	
С	4.40		4.60	0.1732		0.1811	
c1	0.49		0.70	0.0193		0.0276	
c2	2.40		2.72	0.0945		0.1071	
е	2.40		2.70	0.0945		0.1063	
F	6.20		6.60	0.2441		0.2598	
I	3.73		3.88	0.1469		0.1528	
L	2.65		2.95	0.1043		0.1161	
12	1.14		1.70	0.0449		0.0669	
13	1.14		1.70	0.0449		0.0669	
14	15.80	16.40	16.80	0.6220	0.6457	0.6614	
M		2.6			0.1024		

^{1.} Inch dimensions are for reference only.

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3 Ordering information

Figure 15. Ordering information scheme

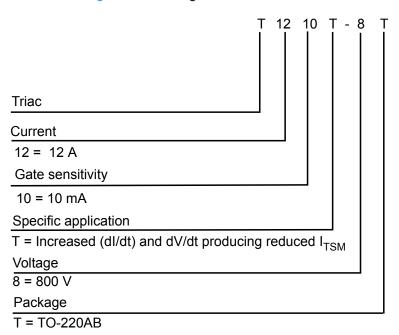


Table 6. Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
T1210T-8T	T1210T-8T	TO-220AB	2.0 g	50	Tube

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Revision history

Table 7. Document revision history

Date	Version	Changes
07-Nov-2014	1	Initial release.
18-Sep-2019	2	Updated Figure 14 and Table 5.



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